MCM67C618B

Product Preview

64K x 18 Bit BurstRAM™ Synchronous Fast Static RAM

With Burst Counter and Registered Outputs

The MCM67C618B is a 1,179,648 bit synchronous static random access memory designed to provide a burstable, high–performance, secondary cache for the i486™ and Pentium™ microprocessors. It is organized as 65,536 words of 18 bits, fabricated with Motorola's high–performance silicon–gate BiCMOS technology. The device integrates input registers, a 2–bit counter, high speed SRAM, and high drive registered output drivers onto a single monolithic circuit for reduced parts count implementation of cache data RAM applications. Synchronous design allows precise cycle control with the use of an external clock (K). BiCMOS circuitry reduces the overall power consumption of the integrated functions for greater reliability.

Addresses (A0 – A15), data inputs (D0 – D17), and all control signals except output enable (G) are clock (K) controlled through positive–edge–triggered noninverting registers.

This device contains output registers for pipeline operations. At the rising edge of K, the RAM provides the output data from the previous cycle.

Output enable (G) is asynchronous for maximum system design flexibility.

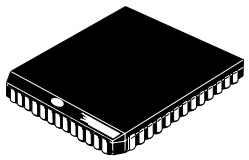
Burst can be initiated with either address status processor (ADSP) or address status cache controller (ADSC) input pins. Subsequent burst addresses can be generated internally by the MCM67C618B (burst sequence imitates that of the i486 and Pentium) and controlled by the burst address advance (ADV) input pin. The following pages provide more detailed information on burst controls.

Write cycles are internally self–timed and are initiated by the rising edge of the clock (K) input. This feature eliminates complex off–chip write pulse generation and provides increased flexibility for incoming signals.

Dual write enables (LW and UW) are provided to allow individually writeable bytes. LW controls DQ0 – DQ8 (the lower bits), while UW controls DQ9 – DQ17 (the upper bits).

This device is ideally suited for systems that require wide data bus widths and cache memory. See Figure 2 for applications information.

- Single 5 V ± 5% Power Supply
- Fast Access Time/Fast Cycle Time = 5 ns/100 MHz, 7 ns/80 MHz
- Byte Writeable via Dual Write Enables
- Internal Input Registers (Address, Data, Control)
- Output Registers for Pipelined Applications
- Internally Self–Timed Write Cycle
- ADSP, ADSC, and ADV Burst Control Pins
- Asynchronous Output Enable Controlled Three–State Outputs
- Common Data Inputs and Data Outputs
- 3.3 V I/O Compatible
- High Board Density 52–Lead PLCC Package

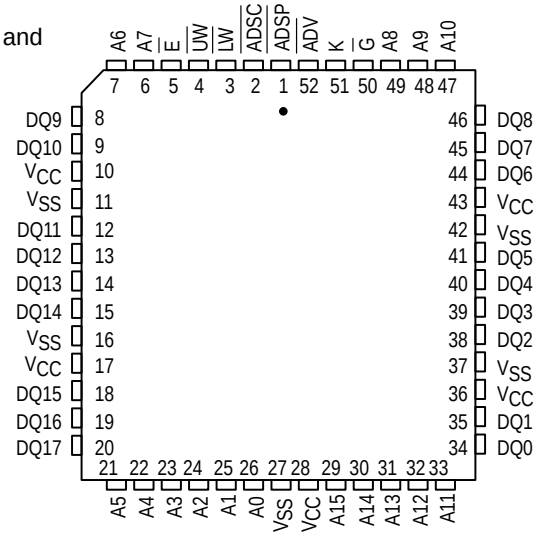


FN PACKAGE
PLASTIC
CASE 778–02

PIN NAMES	
A0 – A15	Address Inputs
K	Clock
ADV	Burst Address Advance
LW	Lower Byte Write Enable
UW	Upper Byte Write Enable
ADSC	Controller Address Status
ADSP	Processor Address Status
E	Chip Enable
G	Output Enable
DQ0 – DQ17	Data Input/Output
V_{CC}	+ 5 V Power Supply
V_{SS}	Ground
NC	No Connection

All power supply and ground pins must be connected for proper operation of the device.

PIN ASSIGNMENT



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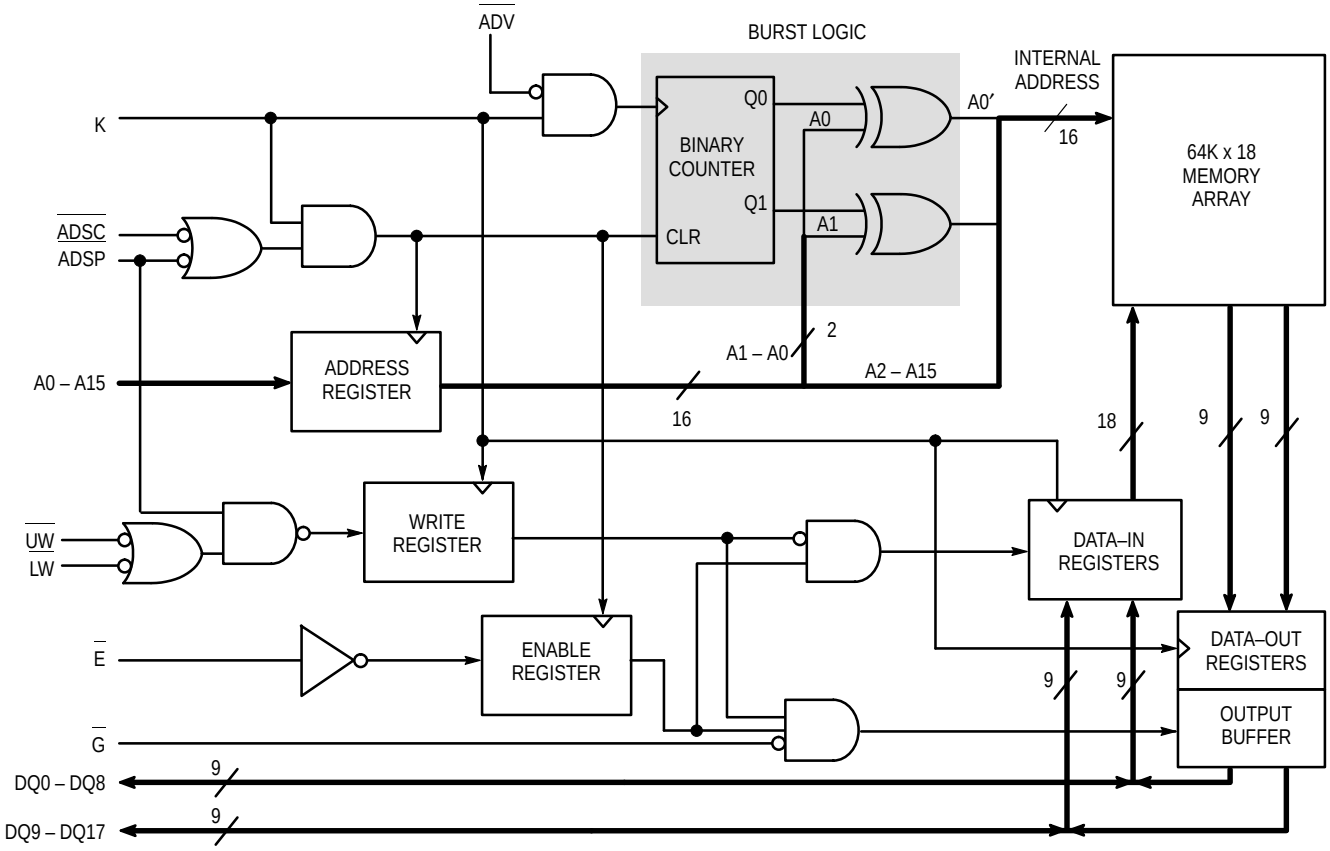
BLOCK DIAGRAM (See Note)



NOTE: All registers are positive–edge triggered. The $\overline{\text{ADSC}}$ or $\overline{\text{ADSP}}$ signals control the duration of the burst and the start of the next burst. When ADSP is sampled low, any ongoing burst is interrupted and a read (independent of W and ADSC) is performed using the new external address. Alternatively, an ADSP–initiated two cycle WRITE can be performed by asserting ADSP and a valid address on the first cycle, then negating both ADSP and ADSC and asserting LW and/or UW with valid data on the second cycle (see Single Write cycle in WRITE CYCLES timing diagram).
When ADSC is sampled low (and ADSP is sampled high), any ongoing burst is interrupted and a read or write (dependent on W) is performed using the new external address. Chip enable (E) is sampled only when a new base address is loaded. After the first cycle of the burst, ADV controls subsequent burst cycles. When ADV is sampled low, the internal address is advanced prior to the operation. When ADV is sampled high, the internal address is not advanced, thus inserting a wait state into the burst sequence accesses. Upon completion of a burst, the address will wrap around to its initial state. See **BURST SEQUENCE TABLE**. Write refers to either or both byte write enables (LW, UW).

BURST SEQUENCE TABLE (See Note)

External Address	A15 – A2	A1	A0
1st Burst Address	A15 – A2	A1	$\overline{\text{A0}}$
2nd Burst Address	A15 – A2	$\overline{\text{A1}}$	A0
3rd Burst Address	A15 – A2	$\overline{\text{A1}}$	$\overline{\text{A0}}$

NOTE: The burst wraps around to its initial state upon completion.

SYNCHRONOUS TRUTH TABLE (See Notes 1, 2, and 3)

E	ADSP	ADSC	ADV	UW or LW	K	Address Used	Operation
H	L	X	X	X	L–H	N/A	Deselected
H	X	L	X	X	L–H	N/A	Deselected
L	L	X	X	X	L–H	External Address	Read Cycle, Begin Burst
L	H	L	X	L	L–H	External Address	Write Cycle, Begin Burst
L	H	L	X	H	L–H	External Address	Read Cycle, Begin Burst
X	H	H	L	L	L–H	Next Address	Write Cycle, Continue Burst
X	H	H	L	H	L–H	Next Address	Read Cycle, Continue Burst
X	H	H	H	L	L–H	Current Address	Write Cycle, Suspend Burst
X	H	H	H	H	L–H	Current Address	Read Cycle, Suspend Burst

NOTES:
1. X means Don't Care.
2. All inputs except G must meet setup and hold times for the low–to–high transition of clock (K).
3. Wait states are inserted by suspending burst.

ASYNCHRONOUS TRUTH TABLE (See Notes 1 and 2)

Operation	G	I/O Status
Read	L	Data Out
Read	H	High–Z
Write	X	High–Z — Data In
Deselected	X	High–Z

NOTES:
1. X means Don't Care.
2. For a write operation following a read operation, $\overline{G}$ must be high before the input data required setup time and held high through the input data hold time.

ABSOLUTE MAXIMUM RATINGS (Voltages Referenced to V_{SS} = 0 V)

Rating	Symbol	Value	Unit
Power Supply Voltage	V_{CC}	– 0.5 to + 7.0	V
Voltage Relative to V_{SS} for Any Pin Except V_{CC}	V_{in}, V_{out}	– 0.5 to V_{CC} + 0.5	V
Output Current (per I/O)	I_{out}	± 30	mA
Power Dissipation	P_D	1.6	W
Temperature Under Bias	T_{bias}	– 10 to + 85	°C
Operating Temperature	T_A	0 to +70	°C
Storage Temperature	T_{stg}	– 55 to + 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high–impedance circuit.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established.

This device contains circuitry that will ensure the output devices are in High–Z at power up.

DC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 5%, T_A = 0 to + 70°C, Unless Otherwise Noted)

RECOMMENDED OPERATING CONDITIONS (Voltages Referenced to V_{SS} = 0 V)

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	V_{CC}	4.75	5.25	V
Input High Voltage	V_{IH}	2.2	V_{CC} + 0.3**	V
Input Low Voltage	V_{IL}	– 0.5*	0.8	V

* V_{IL} (min) = – 0.5 V dc; V_{IL} (min) = – 2.0 V ac (pulse width ≤ 20 ns) for I ≤ 20.0 mA.
** V_{IH} (max) = V_{CC} + 0.3 V dc; V_{IH} (max) = V_{CC} + 2.0 V ac (pulse width ≤ 20 ns) for I ≤ 20.0 mA.

DC CHARACTERISTICS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V_{in} = 0 to V_{CC})	$I_{lkg(I)}$	—	± 1.0	µA
Output Leakage Current (G = V_{IH})	$I_{lkg(O)}$	—	± 1.0	µA
AC Supply Current (G = V_{IH}, E = V_{IL}, I_{out} = 0 mA, All Inputs = V_{IL} or V_{IH}, V_{IL} = 0.0 V and V_{IH} ≥ 3.0 V, Cycle Time ≥ t_{KHKH} min)	I_{CCA5} I_{CCA7}	—	310 290	mA
AC Standby Current (E = V_{IH}, I_{out} = 0 mA, All Inputs = V_{IL} and V_{IH}, V_{IL} = 0.0 V and V_{IH} ≥ 3.0 V, Cycle Time ≥ t_{KHKH} min)	I_{SB1}	—	95	mA
Output Low Voltage (I_{OL} = + 8.0 mA)	V_{OL}	—	0.4	V
Output High Voltage (I_{OH} = – 4.0 mA)	V_{OH}	2.4	3.3	V

NOTE: Good decoupling of the local power supply should always be used. DC characteristics are guaranteed for all possible i486 and Pentium bus cycles.

CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, T_A = 25°C, Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Typ	Max	Unit
Input Capacitance (All Pins Except DQ0 – DQ17)	C_{in}	4	5	pF
Input/Output Capacitance (DQ0 – DQ17)	$C_{I/O}$	6	8	pF

AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 5% T_A = 0 to + 70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level . . . . . 1.5 V
Input Pulse Levels . . . . . 0 to 3.0 V
Input Rise/Fall Time . . . . . 3 ns

Output Timing Reference Level . . . . . 1.5 V
Output Load . . . . . See Figure 1A Unless Otherwise Noted

READ/WRITE CYCLE TIMING (See Notes 1, 2, 3, and 4)

Parameter	Symbol	MCM67C618B–5		MCM67C618B–7		Unit	Notes
		Min	Max	Min	Max		
Cycle Time	t_{KHKH}	10	—	12.5	—	ns	
Clock Access Time	t_{KHQV}	—	5	—	7	ns	5
Output Enable to Output Valid	t_{GLQV}	—	5	—	5	ns	
Clock High to Output Active	t_{KHQX1}	0	—	0	—	ns	
Clock High to Output Change	t_{KHQX2}	2	—	2	—	ns	
Output Enable to Output Active	t_{GLQX}	0	—	0	—	ns	
Output Disable to Q High–Z	t_{GHQZ}	—	6	—	6	ns	6
Clock High to Q High–Z	t_{KHQZ}	2	6	2	6	ns	
Clock High Pulse Width	t_{KHKL}	4.5	—	5	—	ns	
Clock Low Pulse Width	t_{KLKH}	4.5	—	5	—	ns	
Setup Times: Address Address Status Data In Write Address Advance Chip Enable	t_{AVKH} t_{ADSVKH} t_{DVKH} t_{WVKH} t_{ADVVKH} t_{EVKH}	2.5	—	2.5	—	ns	7
Hold Times: Address Address Status Data In Write Address Advance Chip Enable	t_{KHAX} t_{KHADSX} t_{KHDX} t_{KHWX} t_{KHADVX} t_{KHEX}	0.5	—	0.5	—	ns	7

NOTES:
1. In setup and hold times, W (write) refers to either one or both byte write enables $\overline{LW}$ and $\overline{UW}$.
2. A read cycle is defined by UW and LW high or ADSP low for the setup and hold times. A write cycle is defined by $\overline{LW}$ or $\overline{UW}$ low and ADSP high for the setup and hold times.
3. All read and write cycle timings are referenced from K or $\overline{G}$.
4. G is a don't care when UW or LW is sampled low.
5. Maximum access times are guaranteed for all possible i486 and Pentium external bus cycles.
6. Transition is measured ± 500 mV from steady–state voltage with load of Figure 1B. This parameter is sampled rather than 100% tested. At any given voltage and temperature, t_{KHQZ} max is less than t_{KHQZ1} min for a given device and from device to device.
7. This is a synchronous device. All addresses must meet the specified setup and hold times for ***ALL*** rising edges of K whenever $\overline{ADSP}$ or ADSC is low, and the chip is selected. All other synchronous inputs must meet the specified setup and hold times for ***ALL*** rising edges of K when the chip is enabled. Chip enable must be valid at each rising edge of clock for the device (when ADSP or ADSC is low) to remain enabled.

AC TEST LOADS

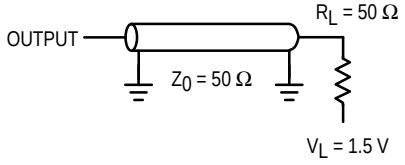


Figure 1A

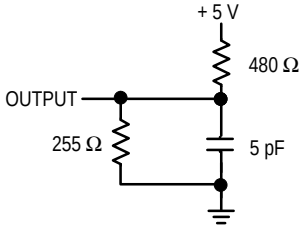
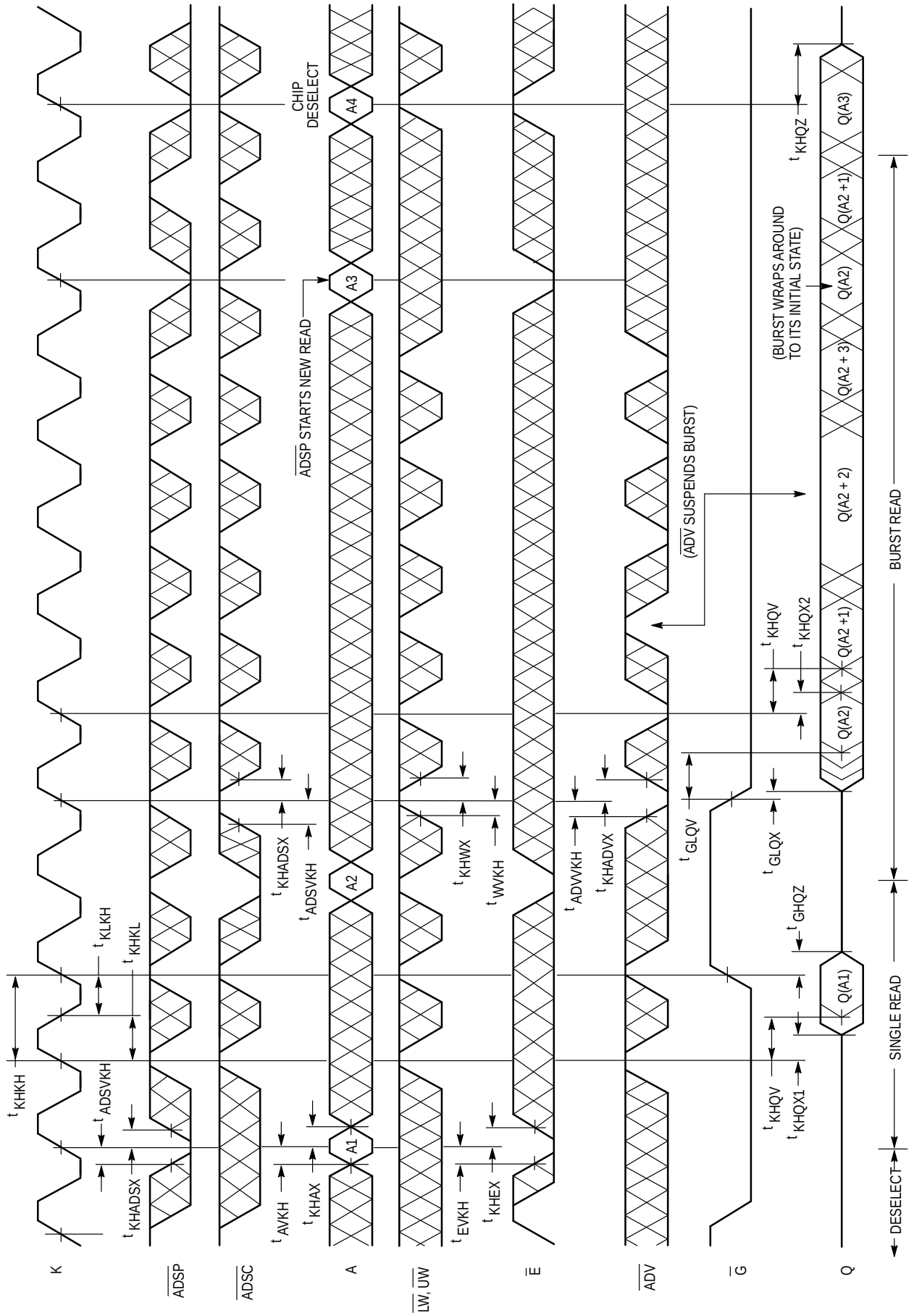
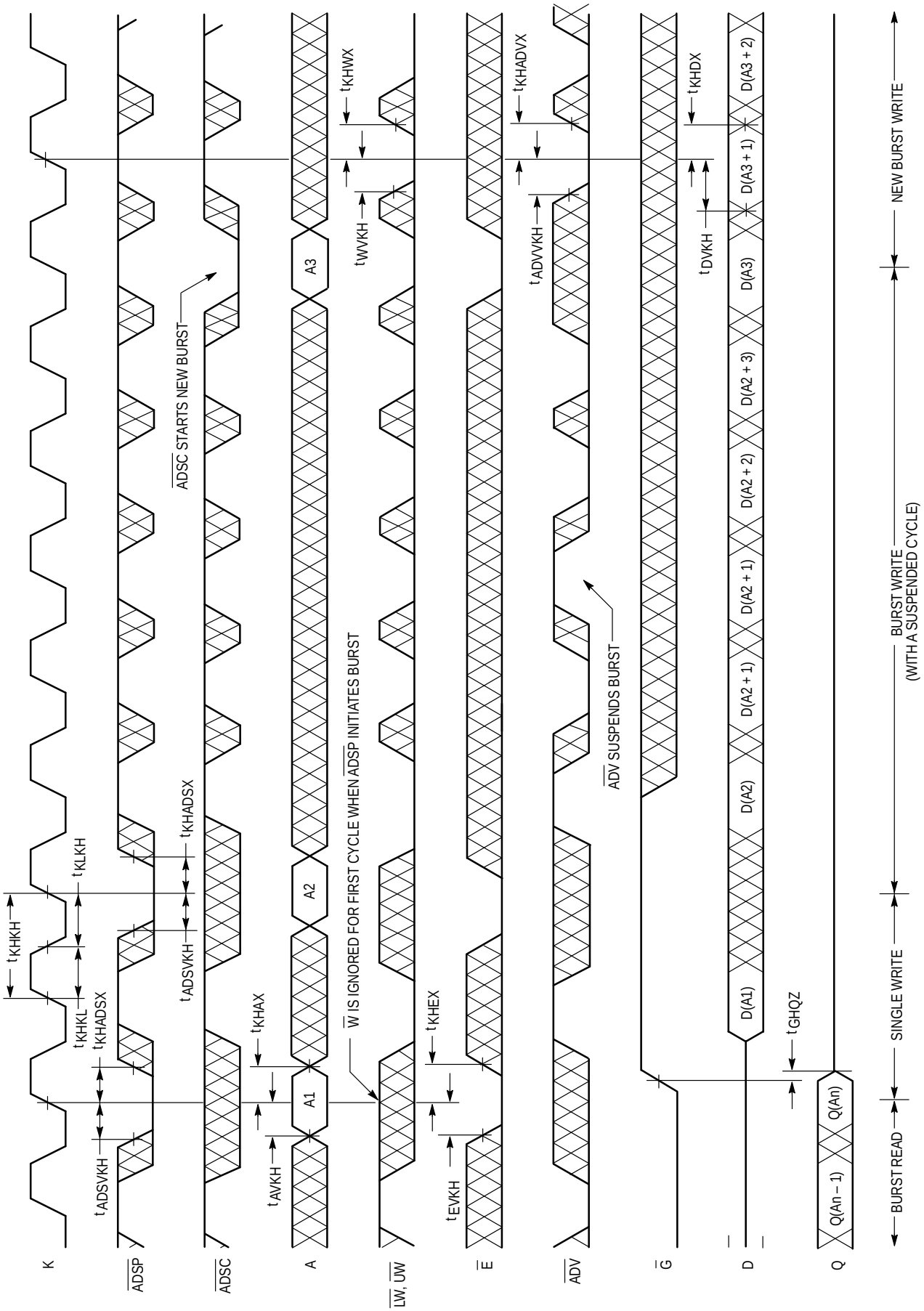


Figure 1B

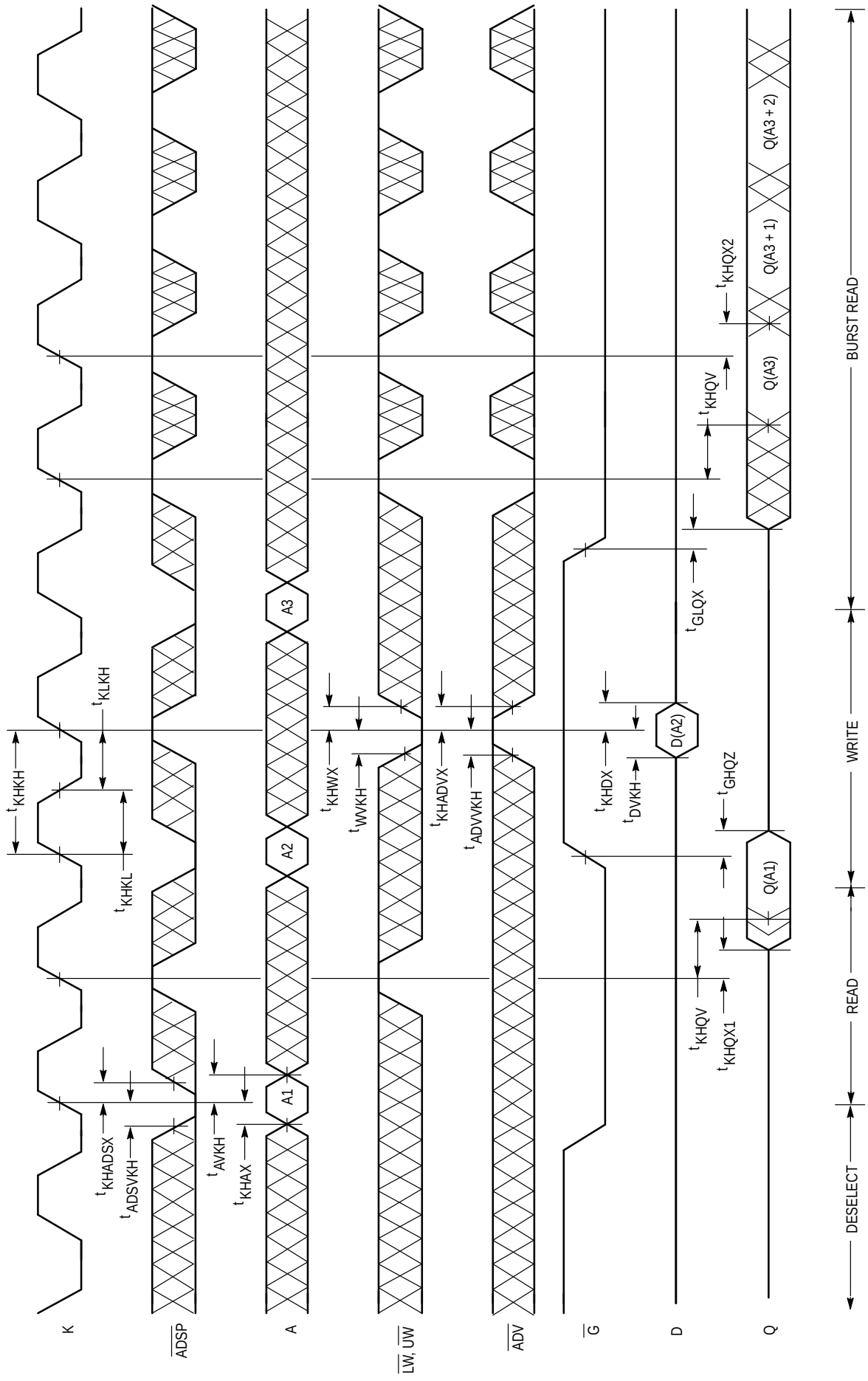
READ CYCLES


K
ADSP
ADSC
A
LW, UW
E
ADV
G
Q
tKHKH
tKLKH
tKHKL
tADSVKH
tKHADSX
tKHADSX
tADSVKH
tAVKH
tKHAX
tKHWX
tWVKH
tEVKH
tKHEX
tADVVKH
tKHADVX
tGLQV
tGLQX
tGHQZ
tKHQV
tKHQX1
tKHQV
tKHQX2
tKHQZ
A1
A2
A3
A4
CHIP DESELECT
ADSP STARTS NEW READ
(ADV SUSPENDS BURST)
(BURST WRAPS AROUND TO ITS INITIAL STATE)
Q(A1)
Q(A2)
Q(A2 +1)
Q(A2 + 2)
Q(A2 + 3)
Q(A2)
Q(A2 +1)
Q(A3)
DESELECT
SINGLE READ
BURST READ

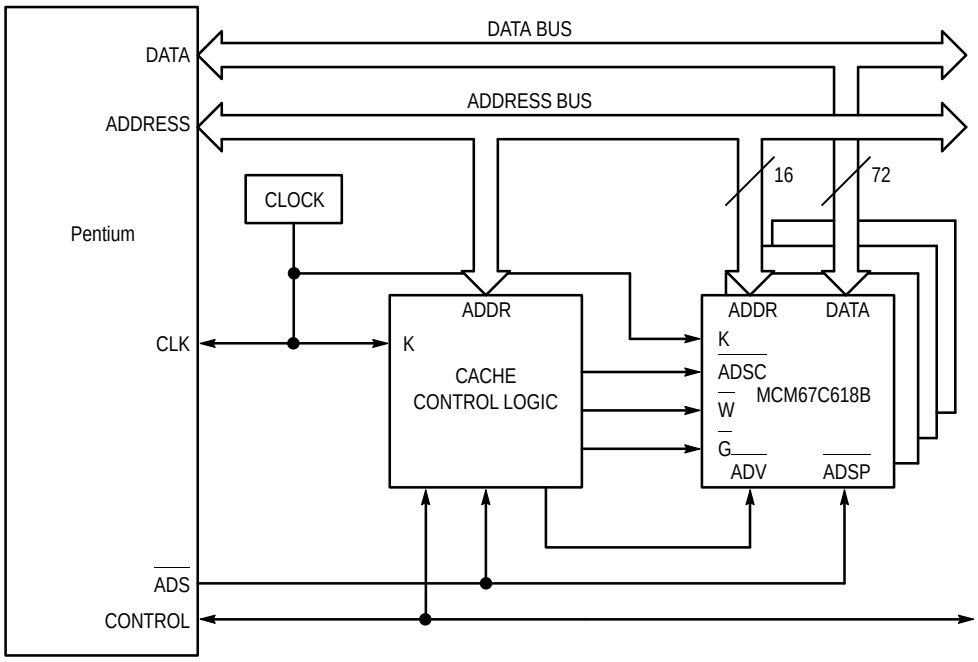
WRITE CYCLES



COMBINATION READ/WRITE CYCLES ($\overline{E}$ Low, $\overline{ADSC}$ High)



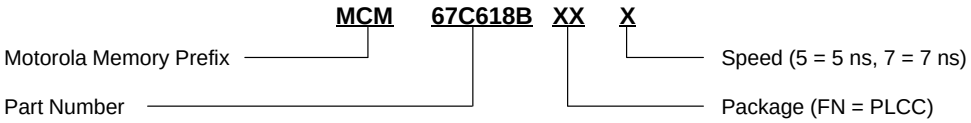
APPLICATION EXAMPLE



512K Byte Burstable, Secondary Cache Using
Four MCM67C618BFN7s With a 75 MHz (bus speed) Pentium

Figure 2

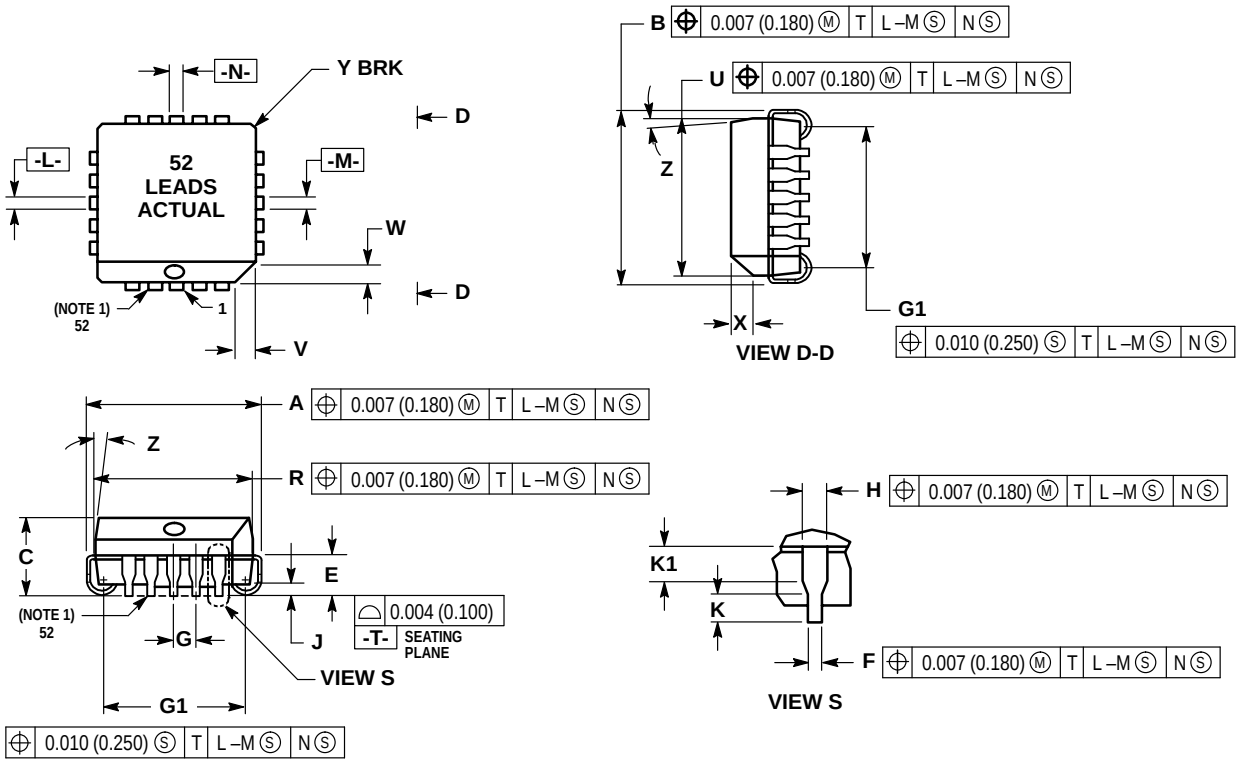
ORDERING INFORMATION
(Order by Full Part Number)



Full Part Numbers — MCM67C618BFN5 MCM67C618BFN7

PACKAGE DIMENSIONS

FN PACKAGE
52–LEAD PLCC
CASE 778–02



NOTES:
1. **DUE TO SPACE LIMITATION, CASE 778-02 SHALL BE REPRESENTED BY A GENERAL (SMALLER) CASE OUTLINE DRAWING RATHER THAN SHOWING ALL 52 LEADS.**
2. DATUMS -L-, -M-, AND -N- DETERMINED WHERE TOP OF LEAD SHOULDER EXITS PLASTIC BODY AT MOLD PARTING LINE.
3. DIM G1, TRUE POSITION TO BE MEASURED AT DATUM -T-, SEATING PLANE.
4. DIM R AND U DO NOT INCLUDE MOLD FLASH. ALLOWABLE MOLD FLASH IS 0.010 (0.250) PER SIDE.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
6. CONTROLLING DIMENSION: INCH.
7. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM BY UP TO 0.012 (0.300). DIMENSIONS R AND U ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.
8. DIMENSION H DOES NOT INCLUDE DAMBAR PROTRUSION OR INTRUSION. THE DAMBAR PROTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE GREATER THAN 0.037 (0.940). THE DAMBAR INTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE SMALLER THAN 0.025 (0.635).

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.785	0.795	19.94	20.19
B	0.785	0.795	19.94	20.19
C	0.165	0.180	4.20	4.57
E	0.090	0.110	2.29	2.79
F	0.013	0.019	0.33	0.48
G	0.050 BSC		1.27 BSC	
H	0.026	0.032	0.66	0.81
J	0.020	—	0.51	—
K	0.025	—	0.64	—
R	0.750	0.756	19.05	19.20
U	0.750	0.756	19.05	19.20
V	0.042	0.048	1.07	1.21
W	0.042	0.048	1.07	1.21
X	0.042	0.056	1.07	1.42
Y	—	0.020	—	0.50
Z	2°	10°	2°	10°
G1	0.710	0.730	18.04	18.54
K1	0.040	—	1.02	—

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